

**Amendments to the Claims**

1. (*Currently Amended*) A semiconductor component comprising a semiconductor chip [[2]] made of a doped silicon substrate, which chip is doped into a semiconductor device and structured, and comprises an inner connection metallization [[7]] in a contact window, and said inner connection metallization of said semiconductor chip is connected to the respective outer connection metallization by a wire bond connection [[9]], characterized in that the inner connection metallization comprises a reinforcing system [[8]] having an open grid structure on the doped silicon substrate.
2. (*Original*) A semiconductor component as claimed in claim 1, characterized in that the reinforcing system having an open grid structure is formed from an insulation coating.
3. (*Original*) A semiconductor component as claimed in claim 1, characterized in that the grid structure is formed so as to be an open groove structure.
4. (*Original*) A semiconductor component as claimed in claim 1, characterized in that the grid structure may be formed so as to be an open tube structure.
5. (*Original*) A semiconductor component as claimed in claim 1, characterized in that the area of the grid structure of thermal oxide constitutes >50% of the area of the contact window.